L Number	Hits	Search Text	DB	Time stamp
1	7	(inorganic adj compound asj solid) and (organic adj	USPAT	2003/04/03 13:15
		substance) and calcining and ferroelectric		
2	0	(inorganic adj compound adj solid) and (organic adj	USPAT	2003/04/03 13:16
		substance) and calcining and ferroelectric		
3	6	(inorganic adj compound ) and (organic adj substance) and	USPAT	2003/04/03 13:18
		calcining and ferroelectric and treatment	001711	2000/01/00 10:10
4	6	(inorganic adj compound ) and (organic adj substance) and	USPAT	2003/04/03 13:27
		calcining and ferroelectric and treatment and oxygen and		2000/01/00 10:2/
		pressure		
5	1	("5156884").PN.	USPAT	2003/04/03 13:27
6	1	("5045348").PN.	USPAT	2003/04/03 13:27
7	1	("4900582").PN.	USPAT	2003/04/03 13:27
8	1229	438/3	USPAT	2003/04/03 13:27
9	632	438/46	USPAT	2003/04/03 13:27
10	232	438/93	USPAT	2003/04/03 13:27
11	167	438/99	USPAT	2003/04/03 13:28
12	35	438/77	USPAT	2003/04/03 13:28
13	377	438/308	USPAT	2003/04/03 13:28
14	228	438/535	USPAT	2003/04/03 13:28
15	139	438/572	USPAT	2003/04/03 13:28
16	207	438/707	USPAT	2003/04/03 13:28
17	605	438/712	USPAT	2003/04/03 13:28
18	192	438/718	USPAT	2003/04/03 13:28
19	756	438/725	USPAT	2003/04/03 13:28
20	103	438/726	USPAT	2003/04/03 13:28
21	549	438/788	USPAT	2003/04/03 13:29
22	340	438/789	USPAT	2003/04/03 13:29
23	374	438/790	USPAT	2003/04/03 13:29
24	262	438/792	USPAT	2003/04/03 13:29
25	60	438/793	USPAT	2003/04/03 13:29
26	52	438/794	USPAT	2003/04/03 13:29
27	684	438/795	USPAT	2003/04/03 13:29
-	19	(capacitor adj containers) and (digit adj line)	USPAT	2003/03/14 13:31
-	0	(capacitor adj containers) and (digit adj line) and (capacitor adj	USPAT	2003/03/14 13:32
	_	formation adj regions)	00171	2003/03/14 13.32
-	1	(capacitor adj containers) and (digit adj line) and (capacitor adj	USPAT	2003/03/14 13:35
	-	formation)	001 A1	2003/03/14 13.33
-	1	("6395600").PN.	USPAT	2003/03/14 13:36
-	1	(("6395600").PN.) and (memory or processor or array or	USPAT	2003/03/16 11:54
	·	plurality or interconnection or interconnected or sidewalls or	001 71	2003/03/10 11.54
		sidewall or capacitor or capcitors or formation or region or		
		regions or digit or line or lines or integrated or circuit or DRAM		
		or HSG or polysilicon or BST ot platinum or TEOS or nitride or		
		silicon or tantalum or barrier or titanium )		
_	1	("5497017").PN.	USPAT	2003/03/14 13:46
_	i	("5998256").PN.	USPAT	2003/03/14 13:46
_	i	(("5497017").PN.) and (memory or processor or array or	USPAT	2003/03/14 13:47
	•	plurality or interconnection or interconnected or sidewalls or	USFAI	2003/03/14 13:48
	ļ	sidewall or capacitor or capcitors or formation or region or		
		regions or digit or line or lines or integrated or circuit or DRAM		
		or HSG or polysilicon or BST of platinum or TEOS or nitride or		
		silicon or tantalum or barrier or titanium )		
	l	omount or taritation of barrier of titalium)		